

SOT-89 Plastic-Encapsulate Transistors

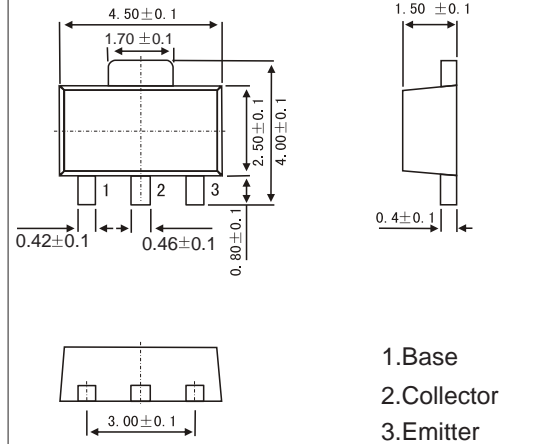
Features

- Low $V_{CE(sat)}$
- Compliments to 2SD1664
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any

SOT-89



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-1	A
Single pulse, $P_w=100ms$		-2	A
Collector Power Dissipation	P_C *	0.5	W
Junction temperature	T_j	150	°C
Storage temperature Range	T_{stg}	-55 to +150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SB1132	SOT-89	3000/Tape&Reel

* When mounted on a 40x40x0.7mm ceramic board.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -50\mu A, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-32			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -50\mu A, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20 V, I_E = 0$			-0.5	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 V, I_C = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 mA, I_B = -50 mA$		-0.2	-0.5	V
DC current gain	h_{FE}	$V_{CE} = -3 V, I_C = -0.1 A$	82		390	
Collector output capacitance	C_{ob}	$V_{CB} = -10 V, I_E = 0 mA, f = 1 MHz$		20	30	pF
Transition frequency	f_T	$V_{CE} = -5 V, I_E = 50 mA, f = 30 MHz$		150		MHz

hFE Classification

Type	2SB1132-P	2SB1132-Q	2SB1132-R
Range	82-180	120-270	180-390
Marking	BAP*	BAQ*	BAR*

■ Typical Characteristics

